

Silicon NPN Power Transistors

2SC1348

DESCRIPTION

- With TO-3 package
- High power dissipation

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
P_C	Collector power dissipation	$T_C = 25 \square$	125	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$; $I_B=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3A$; $I_B=0.6A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=3A$; $I_B=0.6A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=1000V$; $I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=2A$; $V_{CE}=3V$	4.5		19	
f_T	Transition frequency	$I_C=0.5A$; $V_{CE}=10V$		5		MHz

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PACKAGE OUTLINE

